

*“Quantum simulations of electrostatics in Si cylindrical junctionless nanowire nFETs and pFETs with a homogeneous channel including strain and arbitrary crystallographic orientations”*. Pham A-T, Sorée B, Magnus W, Jungemann C, Meinerzhagen B, Pourtois G, Solid state electronics **71**, 30 (2012). <http://doi.org/10.1016/j.sse.2011.10.016>